

Amendments to the Claims

1. (*Currently Amended*) ~~A magnetoresistive~~ A magneto-resistive angle sensor (100) comprising a sensor device for detecting an angle (α) of an external magnetic field relative to a reference axis of the sensor device, characterized in that the sensor device comprises a flat AMR layer (14, 15) with one electrical contact (K0) for applying a current (I) and a plurality of electrical contacts (Ki) for measuring a flow of current through the AMR layer (14, 15).
2. (*Currently Amended*) ~~A magnetoresistive angle sensor as claimed in claim 1, A~~ magneto-resistive angle sensor as claimed in claim 1, characterized in that the sensor device is a circular AMR layer (14).
3. (*Currently Amended*) ~~A magnetoresistive angle sensor as claimed in claim 2, A~~ magneto-resistive angle sensor as claimed in claim 2, characterized in that the electrical contact (K0) for applying a current (I) is arranged in the center of the circular AMR layer (14).
4. (*Currently Amended*) ~~A magnetoresistive angle sensor as claimed in claim 2 or 3, A~~ magneto-resistive angle sensor as claimed in claim 2, characterized in that a plurality of electrical contacts (Ki) are arranged equidistantly at the edge of the circular AMR layer (14), in particular eight electrical contacts.
5. (*Currently Amended*) ~~magnetoresistive angle~~ A magneto-resistive angle as claimed in claim 1, characterized in that the sensor device is a semicircular AMR layer (15).
6. (*Currently Amended*) ~~A magnetoresistive angle~~ A magneto-resistive angle sensor as claimed in claim 5, characterized in that the electrical contact (K0) for applying a current (I) is arranged in the center of an associated full circle.

7. (*Currently Amended*) ~~A magnetoresistive angle sensor as claimed in claim 5 or 6;~~ A magneto-resistive angle sensor s claimed in claim 5, characterized in that a plurality of electrical contacts (K_i) are arranged equidistantly at the semicircular edge of the semicircular AMR layer (15), in particular five electrical contacts.

8. (*Currently Amended*) ~~A magnetoresistive angle sensor as claimed in any of claims 1 to 7;~~ A magneto-resistive angle sensor as claimed in claim 1, characterized in that the plurality of electrical contacts (K_i) are placed at the same potential, in particular at ground potential.

9. (*Currently Amended*) ~~A magnetoresistive angle sensor as claimed in any of claims 1 to 8, as claimed in claim 1, characterized in that the AMR layer (14, 15) is a Permalloy layer, and in particular the latter is applied to a silicon support substrate.~~ A magneto-resistive angle sensor as claimed in claim 1, characterized in that the AMR layer is a Permalloy layer applied to a silicon support substrate.

10. (*Currently Amended*) ~~The use of a magnetoresistive angle sensor (100) as claimed in any of claims 1 to 9 in motor vehicle technology, in particular to monitor the position of a pedal and/or the position of a throttle.~~ The use of a magneto-resistive angle sensor as claimed in claim 1 in motor vehicle technology, wherein the magneto-resistive angle sensor monitors the position of at least one of the following: pedal, throttle.